

TOSHIBA

2SC4209

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC4209

DRIVER STAGE AMPLIFIER APPLICATIONS

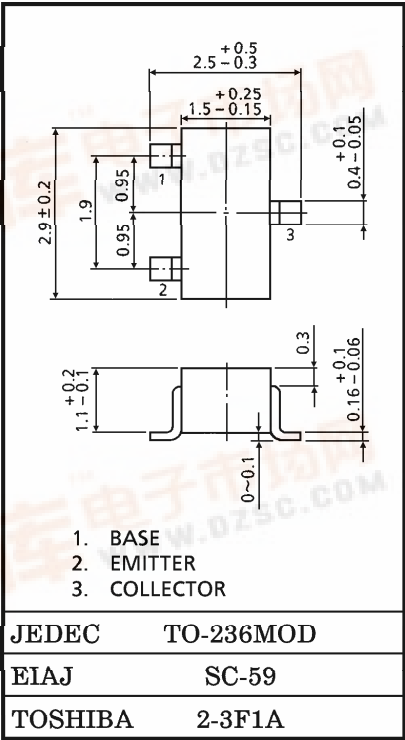
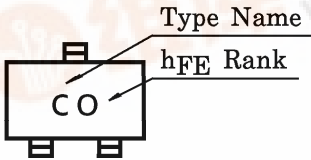
VOLTAGE AMPLIFIER APPLICATIONS

- Complementary to 2SA1620

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	300	mA
Base Current	I _B	60	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	− 55~150	°C

MARKING



Weight : 0.012g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, I_B=0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=2V, I_C=50mA$	70	—	240	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=200mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=10mA$	—	—	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=2V, I_C=5mA$	0.55	—	0.8	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=10mA$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	10	—	pF

(Note) : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

